

INFORMATION DISCLOSURE CITATION PTO-1449	ATTY. DOCKET NO. NTI-007-1D	SERIAL NO. Filed Herewith
	APPLICANT Pierrat, et al.	
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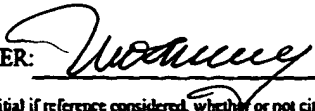
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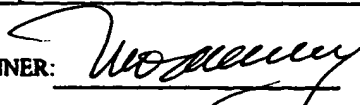
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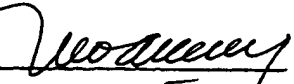
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